











CSD25484F4

SLPS551A-MAY 2015-REVISED AUGUST 2017

# CSD25484F4 -20-V P-Channel FemtoFET™ MOSFET

## **Features**

- Low On-Resistance
- Ultra-Low Q<sub>q</sub> and Q<sub>qd</sub>
- Low-Threshold Voltage
- Ultra-Small Footprint (0402 Case Size)
  - 1.0 mm × 0.6 mm
- Ultra-Low Profile
  - 0.2-mm Height
- Integrated ESD Protection Diode
  - Rated > 4-kV HBM
  - Rated > 2-kV CDM
- Lead and Halogen Free
- **RoHS Compliant**

## 2 Applications

- Optimized for Load Switch Applications
- Optimized for General Purpose Switching **Applications**
- **Battery Applications**
- Handheld and Mobile Applications

## 3 Description

This 80-m $\Omega$ , –20-V, P-Channel FemtoFET<sup>TM</sup> MOSFET is designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing at least a 60% reduction in footprint size.

#### **Product Summary**

$T_A = 25^\circ$	С	TYPICAL VA	UNIT			
$V_{DS}$	Drain-to-Source Voltage –20					
$Q_g$	Gate Charge Total (-4.5 V)	1090		рС		
$Q_{gd}$	Gate Charge Gate-to-Drain	150		рС		
		$V_{GS} = -1.8 \text{ V}$	405			
В	Drain-to-Source	$V_{GS} = -2.5 \text{ V}$	150	mΩ		
R <sub>DS(on)</sub>	On-Resistance	$V_{GS} = -4.5 \text{ V}$	93	11122		
		$V_{GS} = -8.0 \text{ V}$	80	1		
$V_{GS(th)}$	Threshold Voltage	-0.95		V		

#### Device Information<sup>(1)</sup>

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD25484F4	3000		Femto (0402)	Tape
CSD25484F4T	250	7-Inch Reel	1.00-mm × 0.60-mm Land Grid Array (LGA)	and Reel

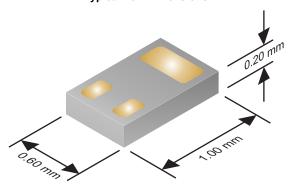
(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### **Absolute Maximum Ratings**

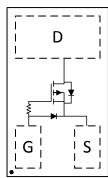
$T_A = 25$	°C	VALUE	UNIT	
$V_{DS}$	Drain-to-Source Voltage	-20	V	
$V_{\text{GS}}$	Gate-to-Source Voltage	-12	V	
$I_D$	Continuous Drain Current <sup>(1)</sup>	-2.5	Α	
I <sub>DM</sub>	Pulsed Drain Current <sup>(1)(2)</sup>	-22	Α	
	Continuous Gate Clamp Current	-35	A	
I <sub>G</sub>	Pulsed Gate Clamp Current <sup>(2)</sup>	-350	mA	
P <sub>D</sub>	Power Dissipation <sup>(1)</sup>	500	mW	
V	Human-Body Model (HBM)	4	kV	
V <sub>(ESD)</sub>	Charged-Device Model (CDM)	2	κV	
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction, Storage Temperature	-55 to 150	°C	

- (1) Typical  $R_{\theta JA} = 85^{\circ}C/W$  on  $1-in^2$  (6.45-cm<sup>2</sup>), 2-oz (0.071-mm) thick Cu pad on a 0.06-in (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤ 100 μs, duty cycle ≤ 1%.

**Typical Part Dimensions** 



#### **Top View**





## **Table of Contents**

1	Features 1	6.1 Receiving Notification of Documentation Updates 7
2	Applications 1	6.2 Community Resources
3	Description 1	6.3 Trademarks
	Revision History2	6.4 Electrostatic Discharge Caution
	Specifications	6.5 Glossary 7
•	5.1 Electrical Characteristics	7 Mechanical, Packaging, and Orderable Information
	5.2 Thermal Information	7.1 Mechanical Dimensions
6	Device and Documentation Support7	7.3 Recommended Stencil Pattern

# 4 Revision History

Page

- Added the Receiving Notification of Documentation Updates and the Community Resources sections to Device and
   Documentation Support
   7

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# 5 Specifications

## 5.1 Electrical Characteristics

 $T_A = 25^{\circ}C$  (unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS					
BV <sub>DSS</sub>	Drain-to-source voltage	$V_{GS} = 0 \text{ V}, I_{DS} = -250  \mu\text{A}$	-20			V
I <sub>DSS</sub>	Drain-to-source leakage current	$V_{GS} = 0 \text{ V}, V_{DS} = -16 \text{ V}$			-100	nA
I <sub>GSS</sub>	Gate-to-source leakage current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = -12 V			-50	nA
V <sub>GS(th)</sub>	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{DS} = -250 \mu A$	-0.7	-0.95	-1.2	V
		$V_{GS} = -1.8 \text{ V}, I_{DS} = -0.1 \text{ A}$		405	825	
D	Droin to course on registance	$V_{GS} = -2.5 \text{ V}, I_{DS} = -0.5 \text{ A}$		150	180	mΩ
R <sub>DS(on)</sub>	Drain-to-source on-resistance	$V_{GS} = -4.5 \text{ V}, I_{DS} = -0.5 \text{ A}$		93	109	11177
		$V_{GS} = -8 \text{ V}, I_{DS} = -0.5 \text{ A}$		80	94	
g <sub>fs</sub>	Transconductance	$V_{DS} = -10 \text{ V}, I_{DS} = -0.5 \text{ A}$		3.5		S
DYNAMI	C CHARACTERISTICS				·	
C <sub>iss</sub>	Input capacitance			175		pF
C <sub>oss</sub>	Output capacitance	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -10 V, f = 1 MHz		78	102	pF
C <sub>rss</sub>	Reverse transfer capacitance	J = 1 Willia		5.5	7.2	pF
R <sub>G</sub>	Series gate resistance			20		Ω
$Q_g$	Gate charge total (-4.5 V)			1090	1415	рС
$Q_{gd}$	Gate charge gate-to-drain	V 40 V I 05 A		150		рС
Q <sub>gs</sub>	Gate charge gate-to-source	$V_{DS} = -10 \text{ V}, I_{DS} = -0.5 \text{ A}$		350		рС
$Q_{g(th)}$	Gate charge at V <sub>th</sub>			210		рС
Q <sub>oss</sub>	Output charge	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V		1290		рС
d(on)	Turnon delay time			9.5		ns
t <sub>r</sub>	Rise time	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		5		ns
t <sub>d(off)</sub>	Turnoff delay time	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$ $I_{DS} = -0.5 \text{ A}, R_G = 10 \Omega$		18		ns
t <sub>f</sub>	Fall Time			8.5		ns
DIODE C	HARACTERISTICS				"	
$V_{SD}$	Diode forward voltage	$I_{SD} = -0.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.75		V
Q <sub>rr</sub>	Reverse recovery charge	V 40 V I 0 5 A 4:/44 400 A / -		970		рС
t <sub>rr</sub>	Reverse recovery time	$V_{DS}$ = -10 V, $I_F$ = -0.5 A, di/dt = 100 A/ $\mu$ s		7.5		ns

## 5.2 Thermal Information

 $T_A = 25$ °C (unless otherwise stated)

	THERMAL METRIC	TYPICAL VALUES	UNIT
В	Junction-to-ambient thermal resistance <sup>(1)</sup>	85	°C/W
$\kappa_{\theta JA}$	Junction-to-ambient thermal resistance <sup>(2)</sup>	245	*C/VV

 <sup>(1)</sup> Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.
 (2) Device mounted on FR4 material with minimum Cu mounting area.

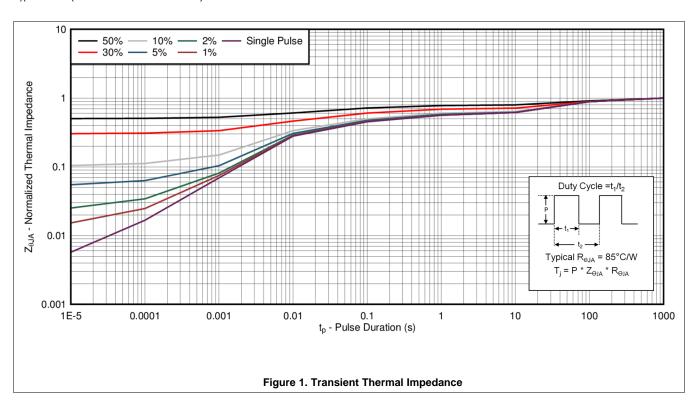
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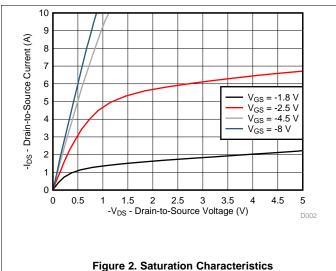
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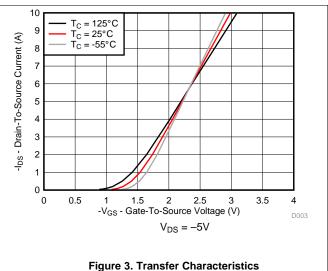
# TEXAS INSTRUMENTS

# 5.3 Typical MOSFET Characteristics

 $T_A = 25$ °C (unless otherwise stated)







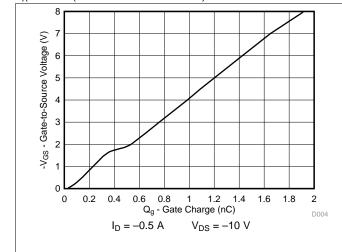
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## **Typical MOSFET Characteristics (continued)**

 $T_A = 25$ °C (unless otherwise stated)



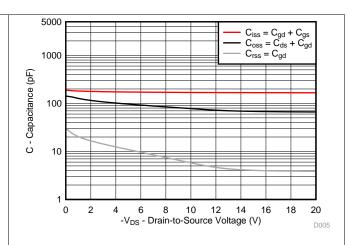


Figure 4. Gate Charge

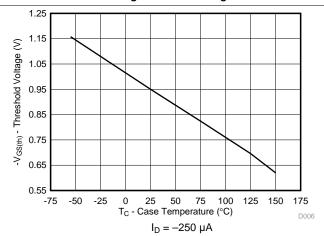


Figure 5. Capacitance

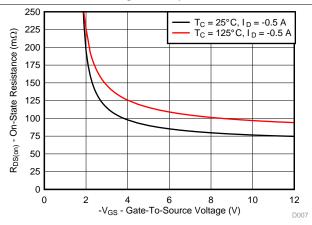


Figure 6. Threshold Voltage vs Temperature

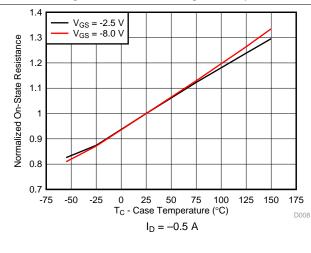


Figure 8. Normalized On-State Resistance vs Temperature

Figure 7. On-State Resistance vs Gate-to-Source Voltage

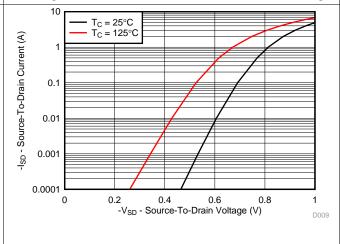
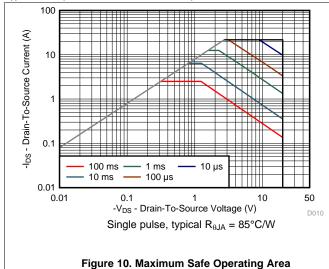


Figure 9. Typical Diode Forward Voltage



# **Typical MOSFET Characteristics (continued)**

 $T_A = 25$ °C (unless otherwise stated)



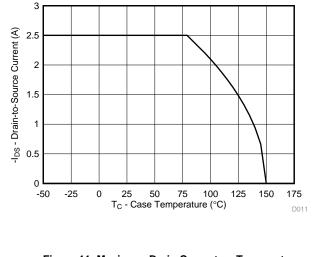


Figure 11. Maximum Drain Current vs Temperature



# 6 Device and Documentation Support

#### 6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 6.3 Trademarks

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All other trademarks are the property of their respective owners.

#### 6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 6.5 Glossary

SLYZ022 — TI Glossary.

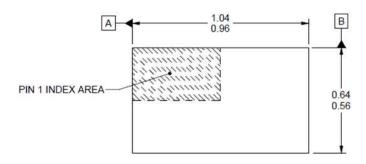
This glossary lists and explains terms, acronyms, and definitions.

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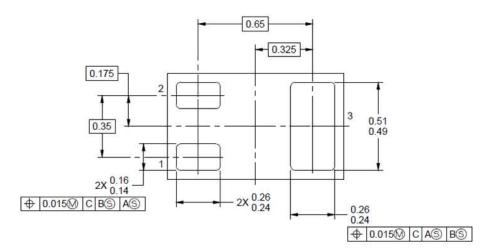
## 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

#### 7.1 Mechanical Dimensions







- (1) All linear dimensions are in millimeters (dimensions and tolerancing per AME T14.5M-1994).
- (2) This drawing is subject to change without notice.
- (3) This package is a PB-free solder land design.

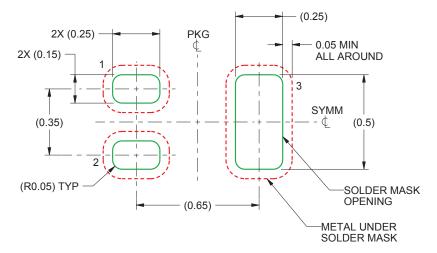
Table 1. Pin Configuration

POSITION	DESIGNATION
Pin 1	Gate
Pin 2	Source
Pin 3	Drain

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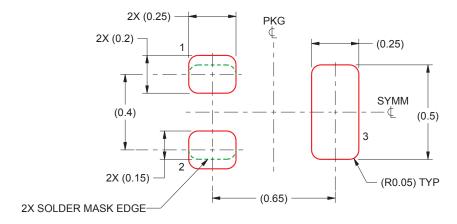


## 7.2 Recommended Minimum PCB Layout



(1) All dimensions are in millimeters.

#### 7.3 Recommended Stencil Pattern



(1) All dimensions are in millimeters.



## PACKAGE OPTION ADDENDUM

3-Aug-2017

#### **PACKAGING INFORMATION**

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Orderable Device	Status	Package Type	_	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD25484F4	ACTIVE	PICOSTAR	YJJ	3	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	G3	Samples
CSD25484F4T	ACTIVE	PICOSTAR	YJJ	3	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	G3	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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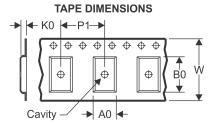
3-Aug-2017

PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD25484F4	PICOST AR	YJJ	3	3000	178.0	9.2	0.7	1.1	0.28	4.0	8.0	Q2
CSD25484F4T	PICOST AR	YJJ	3	250	178.0	9.2	0.7	1.1	0.28	4.0	8.0	Q2

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#### \*All dimensions are nominal

I	Device	Device Package Type Package Di		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
	CSD25484F4	PICOSTAR	YJJ	3	3000	220.0	220.0	35.0
	CSD25484F4T	PICOSTAR	YJJ	3	250	220.0	220.0	35.0

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